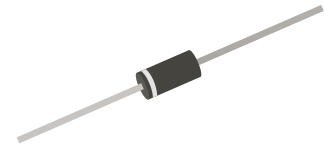


SB520-G Thru. SB5100-G

Voltage: 20 to 100 V

Current: 5.0 A

RoHS Device

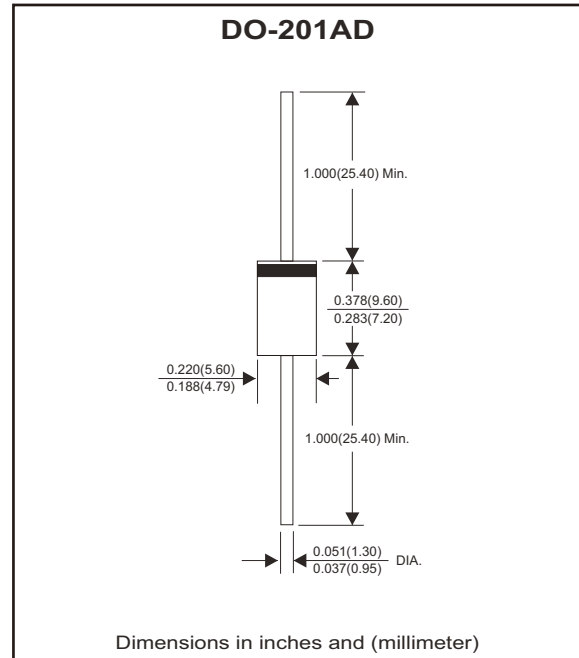


Features

- Low drop down voltage.
- Metal-Semiconductor junction with guard ring
- High surge current capability
- Silicon epitaxial planar chips.
- For use in low voltage, high efficiency inverters, free wheeling, and polarity protection applications
- Lead-free part, meet RoHS requirements.

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case: Molded plastic body DO-201AD
- Terminals: Solderable per MIL-STD-750 Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 1.12 grams (approx.).



Circuit Diagram



Electrical Characteristics (at TA=25°C unless otherwise noted)

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	SB 520-G	SB 540-G	SB 545-G	SB 550-G	SB 560-G	SB 580-G	SB 5100-G	Unit	
Maximum recurrent peak reverse voltage	V _{RRM}	20	40	45	50	60	80	100	V	
Maximum RMS voltage	V _{RMS}	14	28	30	35	42	56	70	V	
Maximum DC blocking voltage	V _{DC}	20	40	45	50	60	80	100	V	
Maximum average forward rectified current 0.5" (12.7mm) lead length at TA=75°C, See Figure 1	I _(AV)	5.0								A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method) TL=110°C	I _{FSM}	100								A
Maximum forward voltage at 5.0A (Note 1)	V _F	0.55		0.70		0.85			V	
Maximum DC reverse current At rated DC blocking voltage	T _J =25°C	0.5							mA	
	T _J =100°C	50		30						
Typical junction capacitance (Note 2)	C _J	350		135				pF		
Typical thermal resistance (Note 3)	R _{θJA}	35							°C/W	
	R _{θJL}	15								
Operating junction temperature range	T _J	-65 to +150							°C	
Storage temperature range	T _{STG}	-65 to +150							°C	

NOTES:

1. Pulse test 300µs pulse width, 1% duty cycle.
2. Measured at 1.0MHz and applied reverse voltage of 4.0 Volts.
3. Thermal resistance junction to ambient and from junction to lead P.C.B mounted 0.500"(12.7mm)lead length with 2.5*2.5"(63.5*63.5mm) copper pad.

Company reserves the right to improve product design , functions and reliability without notice.

REV:C

RATING AND CHARACTERISTIC CURVES (SB520-G Thru. SB5100-G)

Fig.1 - Forward Current Derating Curve

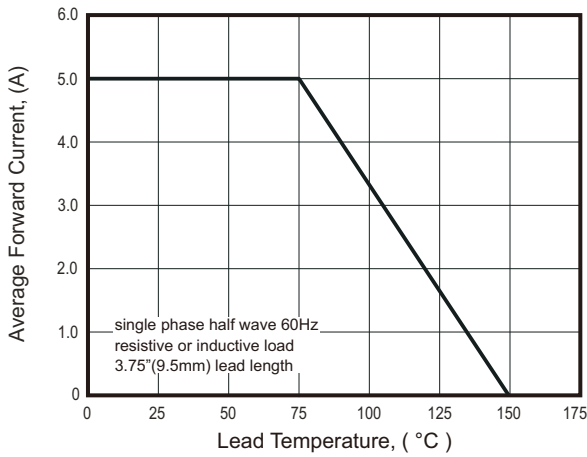


Fig.2 - Maximum Non-repetitive Peak Forward Surge Current

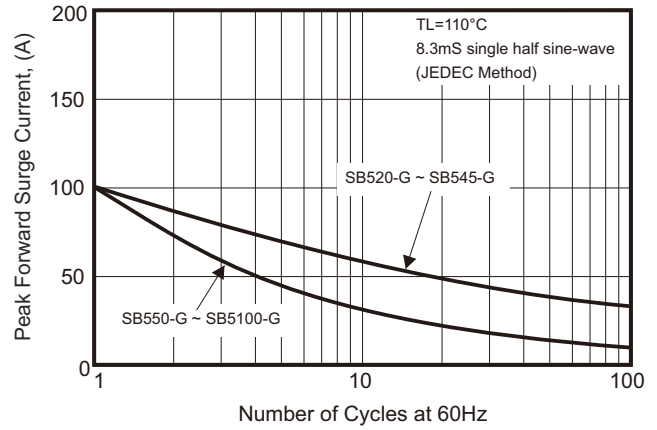


Fig.3 - Typical Instantaneous Forward Characteristics

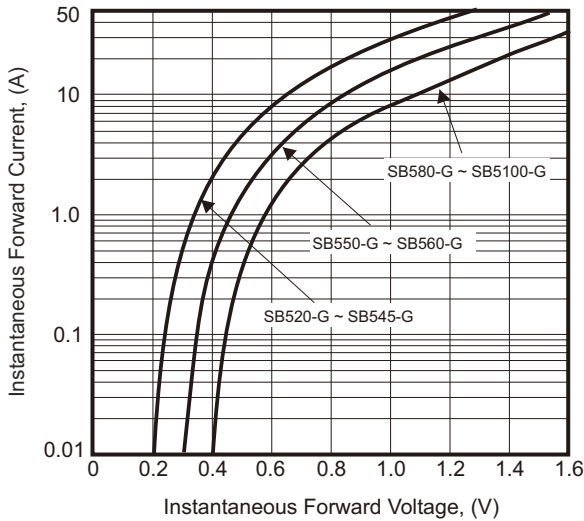


Fig.4A - Typical Reverse Characteristics

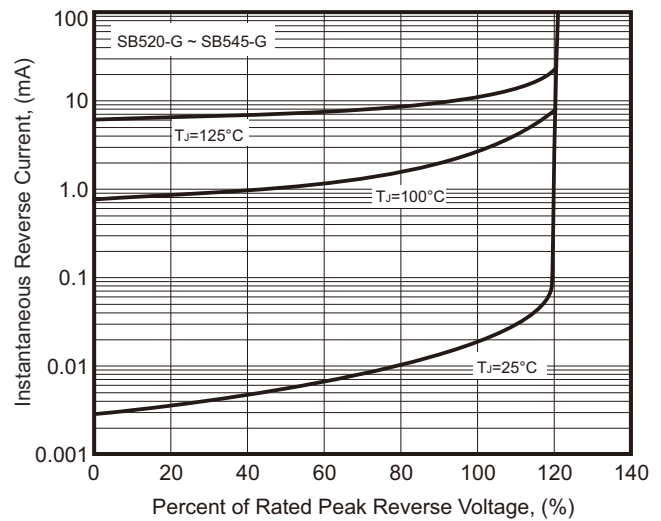


Fig.5 - Typical Junction Capacitance

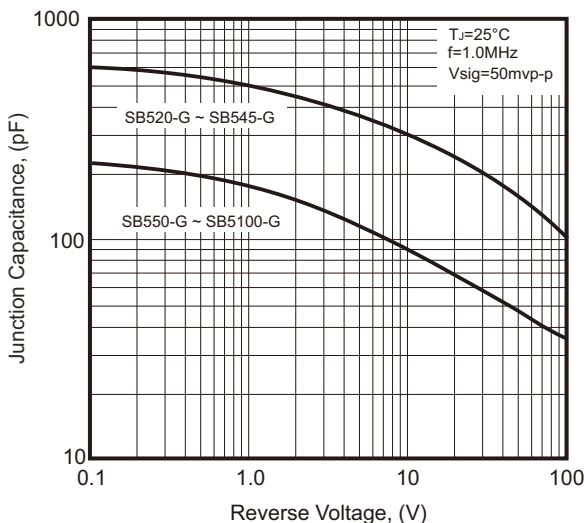
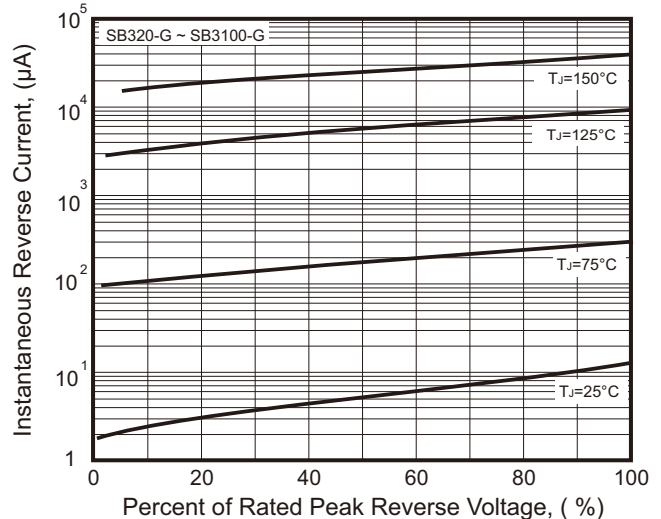
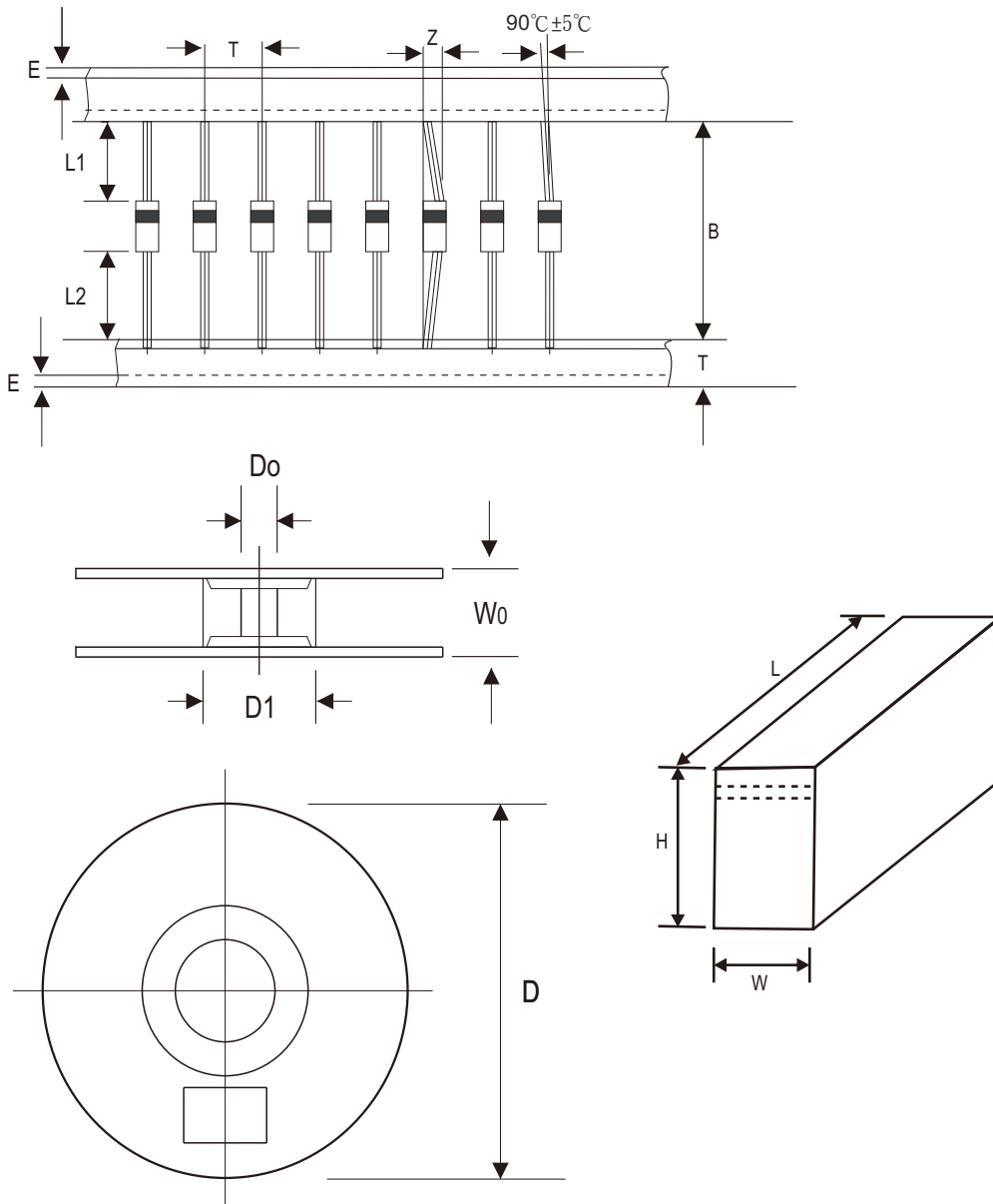


Fig.4B - Typical Reverse Characteristic



Taping Specification For Axial Lead Diodes



DO-201AD	SYMBOL	A	B	Z	T	E	L1-L2
	(mm)	10.00 ± 0.50	52.40 ± 1.50	1.60(max)	6.00 ± 0.40	3.00(max)	1.00(max)
	(inch)	0.394 ± 0.020	2.063 ± 0.059	0.063(max)	0.236 ± 0.016	0.118(max)	0.039(max)

DO-201AD	SYMBOL	D	Do	D1	W0
	(mm)	330.00	16.60 ± 0.40	82.20 ± 0.30	77.00 ± 1.00
	(inch)	12.992	0.654 ± 0.016	3.236 ± 0.012	3.031 ± 0.039

DO-201AD	SYMBOL	Box Length	Box Width	Box Height
	(mm)	260.00 ± 5.00	80.00 ± 5.00	145.00 ± 5.00
	(inch)	10.236 ± 0.197	3.150 ± 0.197	5.709 ± 0.197

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